

Product Summary

BV_{DSS}	R_{D(S)}(ON)	I_D T_A = +25°C
100V	700mΩ @ V _{GS} = 10V	0.70A
	900mΩ @ V _{GS} = 6.0V	0.62A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{D(S)}(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

Features and Benefits

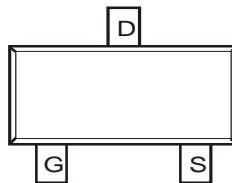
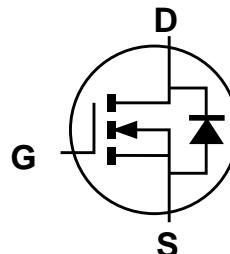
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish Annealed over Alloy 42 Leadframe). (③)
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)



Top View


 Top View
 Pin Configuration


Equivalent Circuit

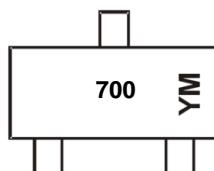
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN10H700S-7	SOT23	3,000/Tape & Reel
DMN10H700S-13	SOT23	10,000/Tape & Reel

Notes:

- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



700 = Product Type Marking Code
 YM = Date Code Marking
 Y or YM = Year (ex: E = 2017)
 M = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	
Code	C	D	E	F	G	H	I	J	K	L	M	
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	100	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	0.70 0.56	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle $\leq 1\%$)			I_{DM}	2.5	A
Maximum Body Diode Continuous Current (Note 6)			I_S	0.6	A

 Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation	(Note 5)	P_D	0.4	W
	(Note 6)		0.5	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	303	°C/W
		$R_{\theta JA}$	239	
		$R_{\theta JC}$	88	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

 Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	100	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 100\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	2.0	2.7	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	540	700	mΩ	$V_{GS} = 10\text{V}, I_D = 1.5\text{A}$
		—	550	900		$V_{GS} = 6.0\text{V}, I_D = 1.0\text{A}$
Diode Forward Voltage	V_{SD}	—	0.9	1.1	V	$V_{GS} = 0\text{V}, I_S = 1.5\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	235	—	pF	$V_{DS} = 50\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	7	—		
Reverse Transfer Capacitance	C_{rss}	—	5	—		
Gate Resistance	R_G	—	1.9	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge	Q_g	—	4.6	—		
Gate-Source Charge	Q_{gs}	—	1.1	—		
Gate-Drain Charge	Q_{gd}	—	1.6	—		
Turn-On Delay Time	$t_{D(ON)}$	—	2.5	—	ns	$V_{DS} = 50\text{V}, I_D = 1.0\text{A}, V_{GS} = 10\text{V}, I_D = 1.0\text{A}$
Turn-On Rise Time	t_R	—	1.1	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	5.4	—		
Turn-Off Fall Time	t_F	—	1.0	—		
Reverse Recovery Time	t_{RR}	—	22	—	ns	$V_R = 100\text{V}, I_F = 1.8\text{A}, dI/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge	Q_{RR}	—	15	—		

Notes:

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

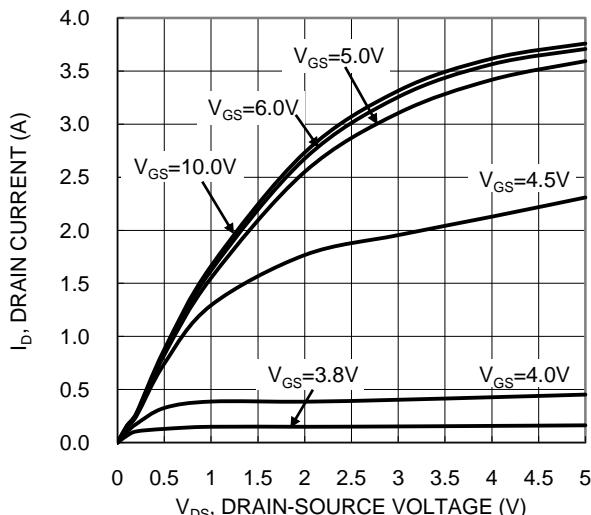


Figure 1. Typical Output Characteristic

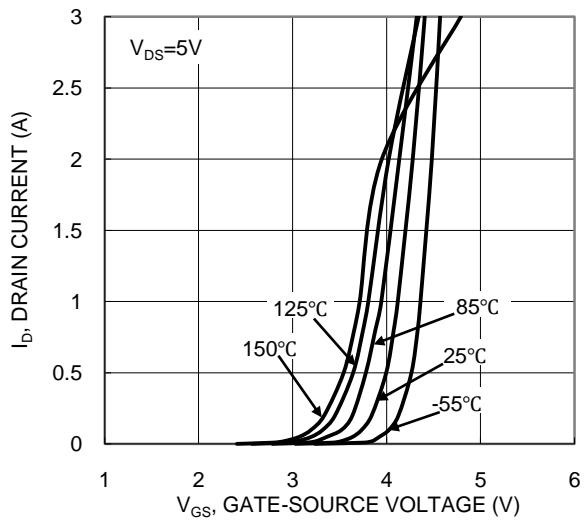


Figure 2. Typical Transfer Characteristic

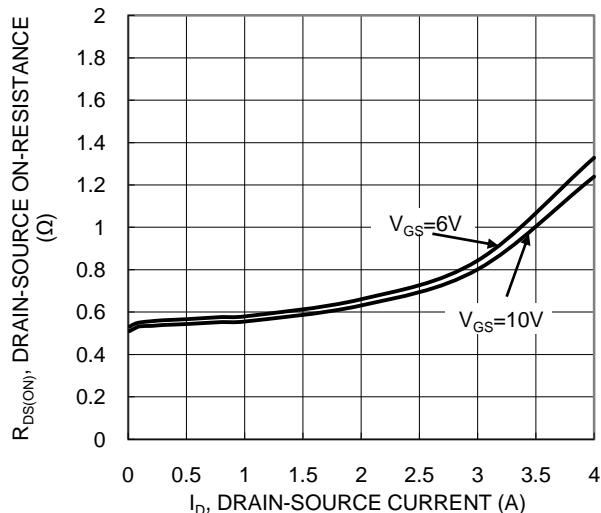


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

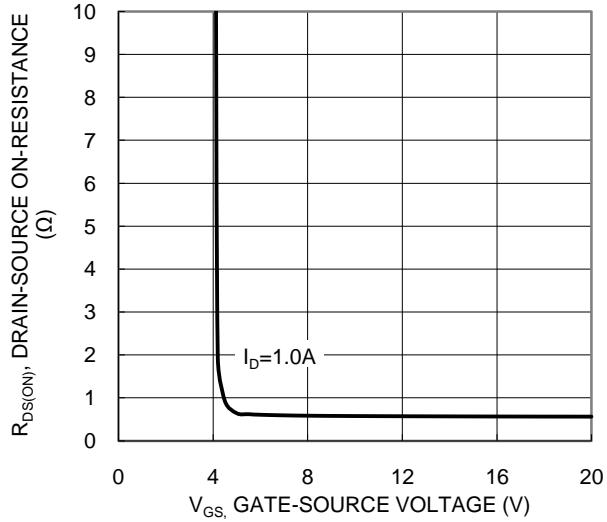


Figure 4. Typical Transfer Characteristic

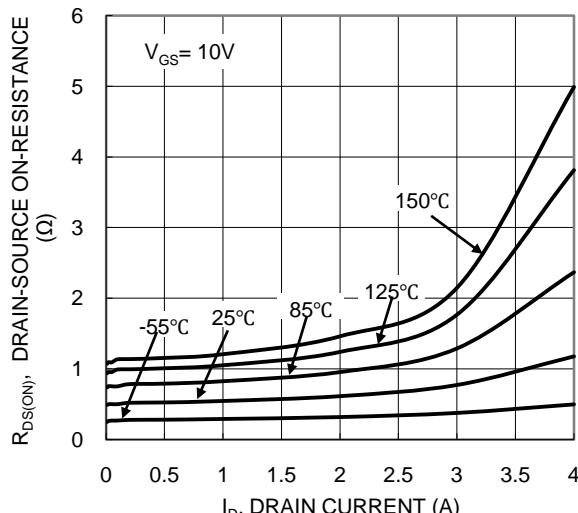


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

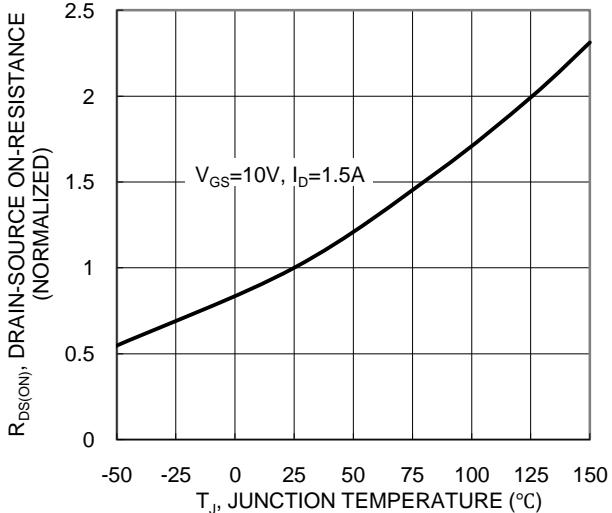


Figure 6. On-Resistance Variation with Junction Temperature

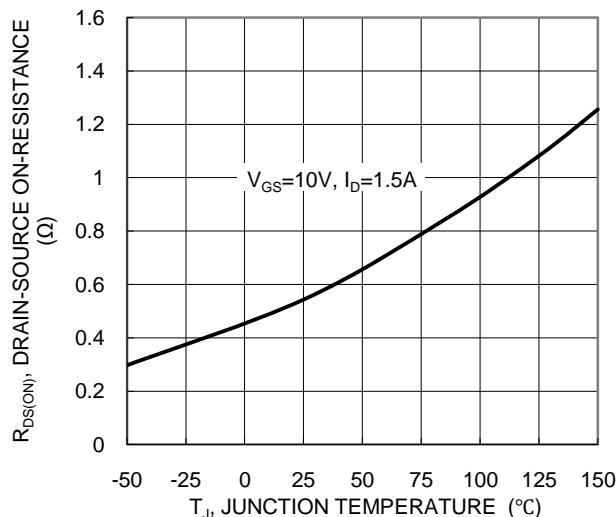


Figure 7. On-Resistance Variation with Junction Temperature

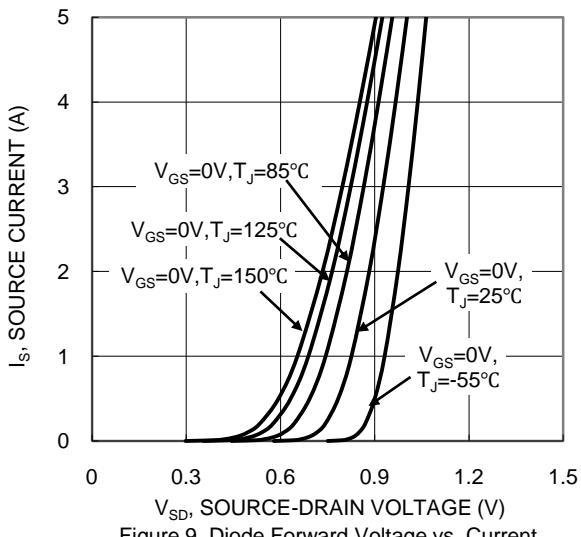


Figure 9. Diode Forward Voltage vs. Current

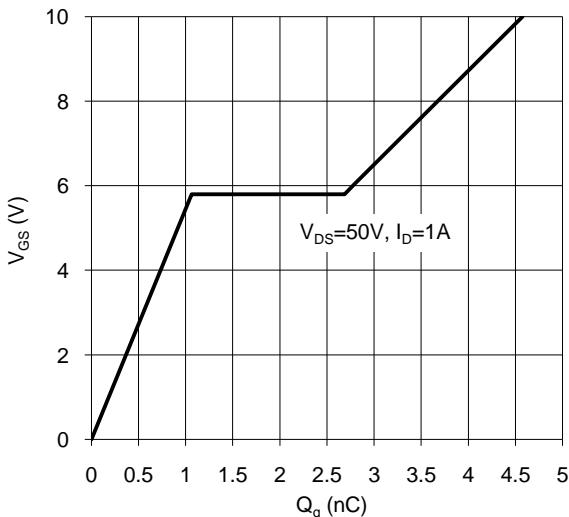


Figure 11. Gate Charge

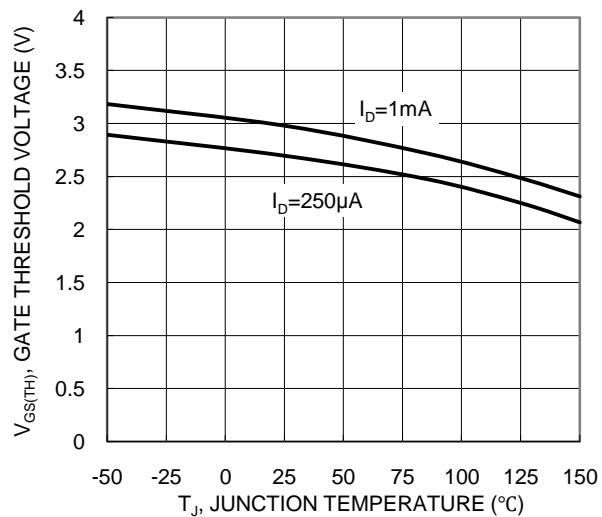


Figure 8. Gate Threshold Variation vs. Junction Temperature

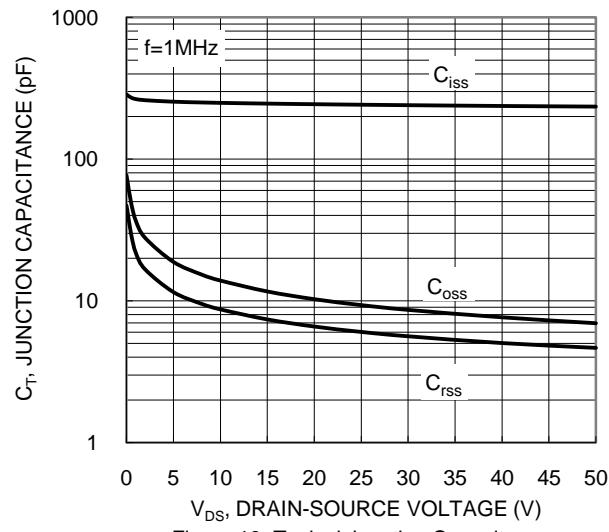


Figure 10. Typical Junction Capacitance

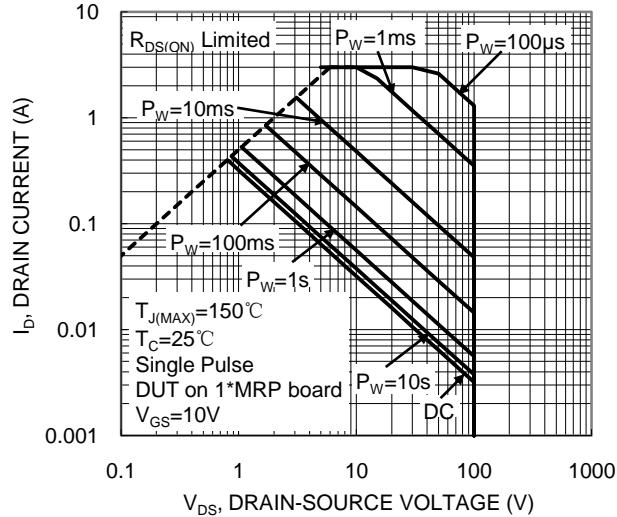


Figure 12. SOA, Safe Operation Area

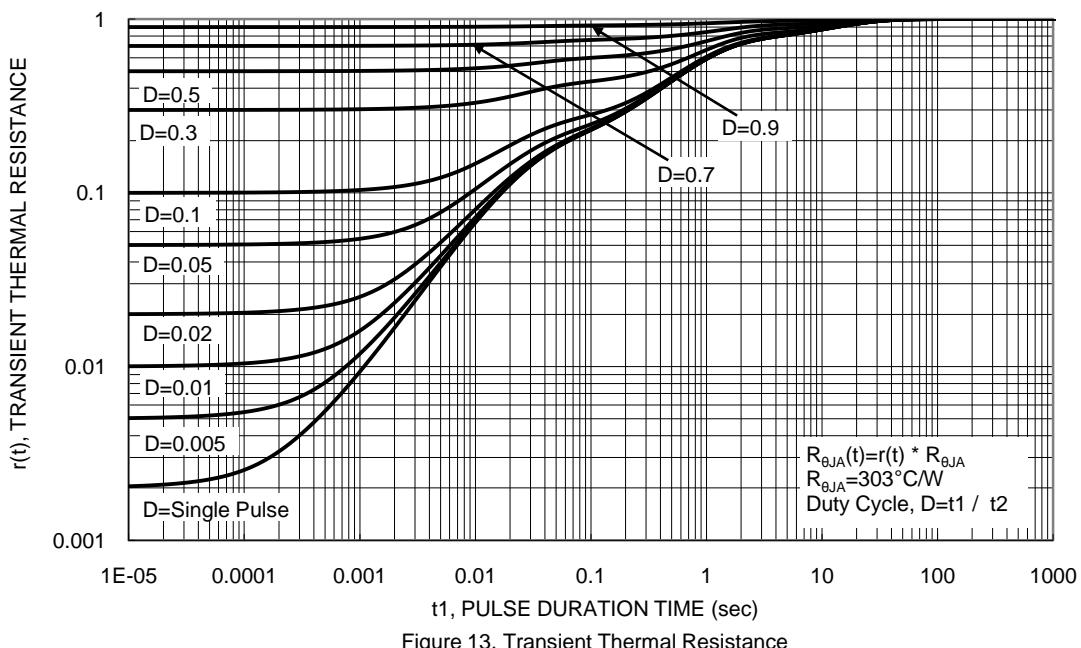
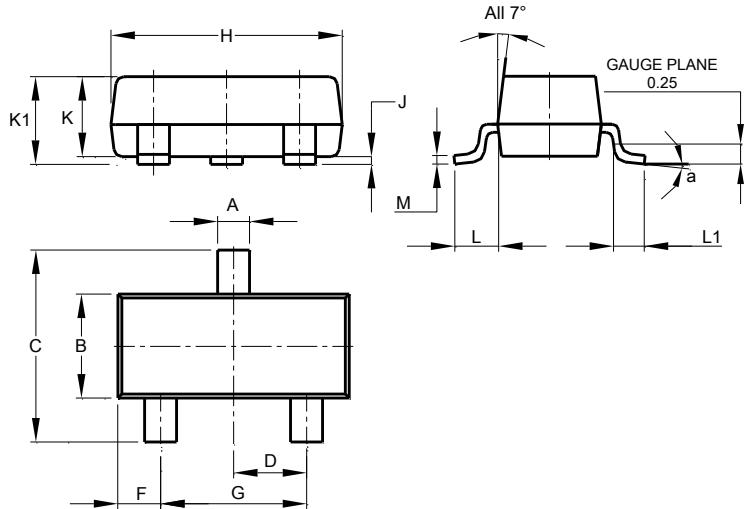


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



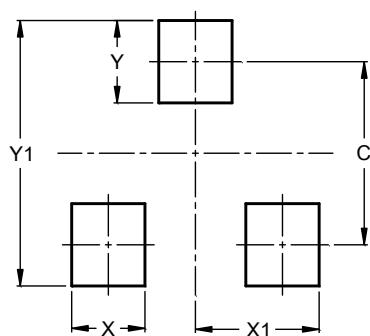
SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--

All Dimensions in mm

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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